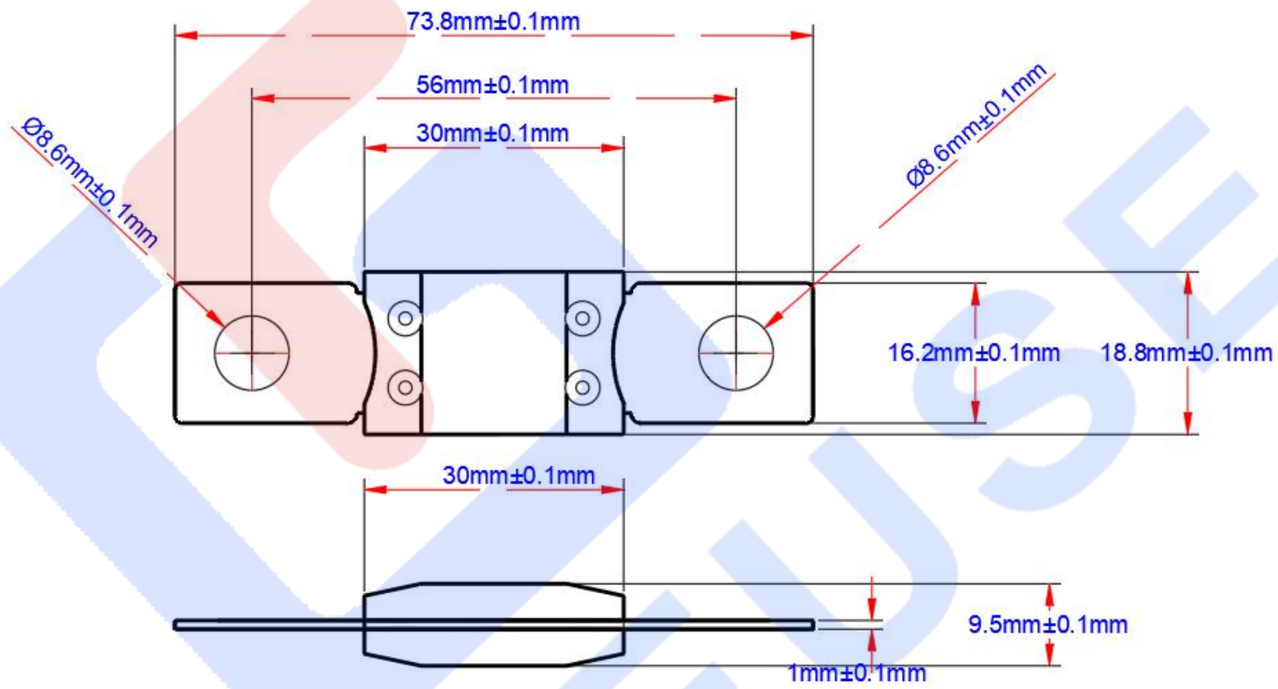
ANL-B200ASF56 Bolt-Down Ess Fuse

1.Dimensions (mm)



2.Specifications

- Product Features
- Compact design, suitable for high current applications.
- Rated DC voltage of 175 volts
- Shell material: high-temperature PPS and ceramic
- The product complies with UL248-13 standard
- High current wire protection
- Vehicle distribution (electric motorcycles, new energy trams, charging supporting systems)
- Material processing system
- Unmanned aerial vehicle power distribution protection
- All supercapacitor and battery systems (energy storage protection system)
- Operating temperature -40 ° C to+125 ° C

3. Time-Current Characteristics

% of Rating	Opening Time Min / Max
	100A - 700A
100	4H / ∞
300	~/10S

4.Product specifications

Part Number	Rating Current(A)	Pre-arcing I²t(A²s)	Arcing I²t(A²s)	Total Clearing I²t(A²s)
ANL-B200A100SF56	100A	520	182	702
ANL-B200A150SF56	150A	980	280	1260
ANL-B200A200SF56	200A	1650	434	2084
ANL-B200A250SF56	250A	2600	665	3265
ANL-B200A300SF56	300A	3750	980	4730
ANL-B200A350SF56	350A	5100	1330	6430
ANL-B200A400SF56	400A	6800	1785	8585
ANL-B200A450SF56	450A	8250	2258	10508
ANL-B200A500SF56	500A	10800	2800	13600
ANL-B200A550SF56	550A	13100	3390	16495
ANL-B200A600SF56	600A	15600	3990	19590
ANL-B200A650SF56	650A	18250	4585	22835
ANL-B200A700SF56	700A	21000	5180	26180

1. With a short-circuit current of 20kA and a relatively high interruption current, the melting and arcing energy is reduced simultaneously, resulting in a faster breaking speed and less impact on power devices.
2. The overload operating threshold and voltage drop remain unchanged, and the long-term current carrying capacity is not affected by the short circuit level.
3. This breakout specification meets the protection requirements of conventional low-voltage DC busbars, energy storage auxiliary circuits, and industrial control DC equipment.
4. The system short-circuit current is stable within 20kA, and this set of parameters can be directly used for device I^2t matching verification.
5. It exhibits good arc extinction stability in low-voltage and low-interruption scenarios, and can be normally adapted to circuits with L/R ≤ 25ms.
6. When selecting a device, a protection margin should be reserved, and the total breaking capacity I²t must be less than the withstand limit of the semiconductor device.

5：Time-Current Characteristic Curves